MOSFETs Silicon N-Channel MOS

# SSM3K318R

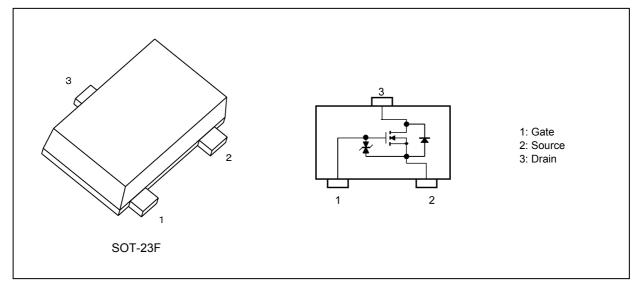
### 1. Applications

- Load Switches
- Ultra-High-Speed Switching

### 2. Features

- (1) 4.5-V gate drive voltage.
- $\begin{array}{ll} \mbox{(2)} & \mbox{Low drain-source on-resistance} \\ & \mbox{$R_{\rm DS(ON)}=145$ m}\Omega\mbox{$(max)$ (@V_{\rm GS}=4.5$ V)$} \\ & \mbox{$R_{\rm DS(ON)}=107$ m}\Omega\mbox{$(max)$ (@V_{\rm GS}=10$ V)$} \end{array}$

### 3. Packaging and Pin Assignment



#### 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C)

	Characteristics		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	60	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current		(Note 1)	I <sub>D</sub>	2.5	A
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	5	
Power dissipation		(Note 2)	PD	1	W
Power dissipation	(t = 10 s)	(Note 2)	PD	2	]
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Device mounted on an FR4 board. (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm ,Cu pad: 645 mm<sup>2</sup>)

- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Electrical Characteristics

#### 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS}$ = ±16 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	_		1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	60	—	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	35	_	_	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 1 mA	1.8	—	2.8	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	$I_D$ = 2.0 A, $V_{GS}$ = 10 V	_	83.5	107	mΩ
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 4.5 V	_	101	145	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 2 A	3.7	7.4	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

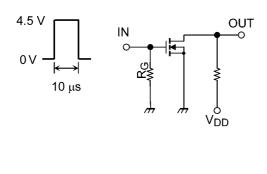
Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V,	_	235	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	23	_	
Output capacitance	C <sub>oss</sub>		_	31	_	
Switching time (turn-on time)	t <sub>on</sub>	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 1 A,	_	14	_	ns
Switching time (turn-off time)	t <sub>off</sub>	$V_{GS}$ = 0 to 4.5 V, $R_{G}$ = 10 $\Omega$	_	9.5	_	

### 5.3. Switching Time Test Circuit



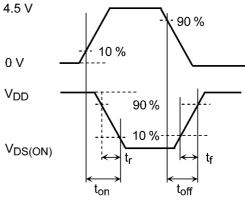


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

#### 5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

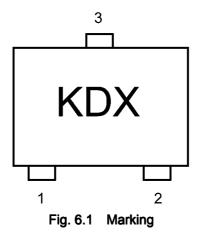
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 2.5 A,	_	7	_	nC
Gate-source charge	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	—	4.8	—	
Gate-drain charge	Q <sub>gd</sub>			2.2	_	

### 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

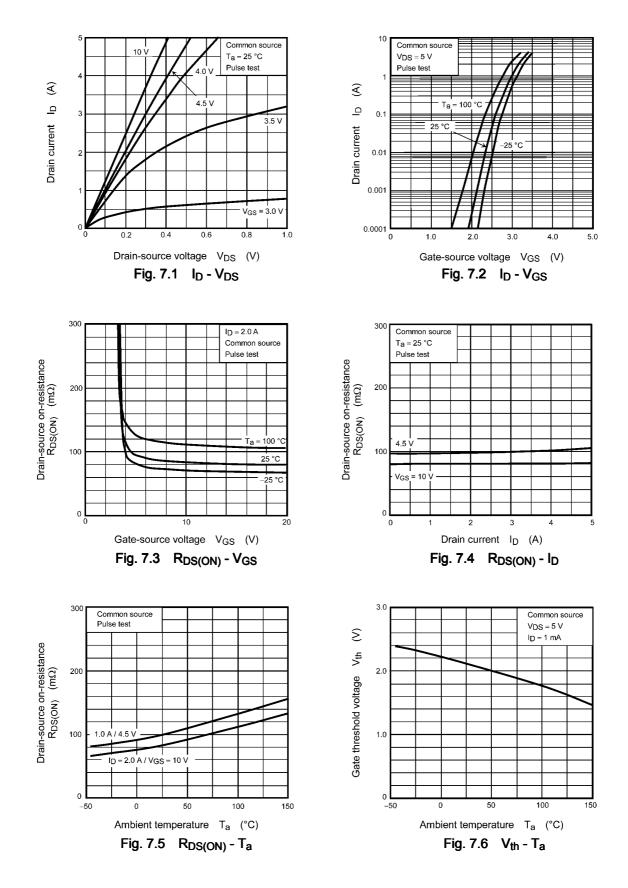
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage (Note	1) V <sub>DSF</sub>	$I_{\rm D}$ = -2.5 A, $V_{\rm GS}$ = 0 V		-0.83	-1.2	V

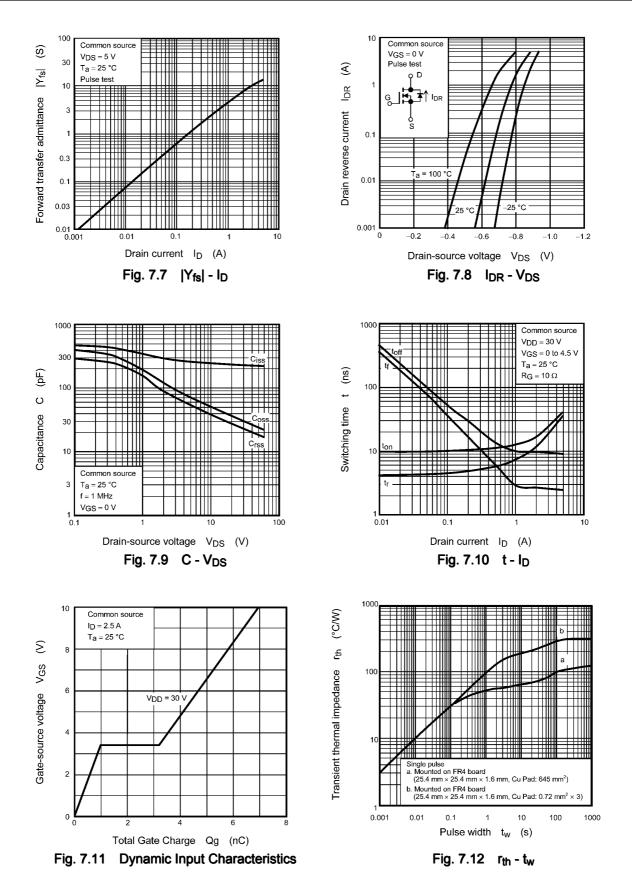
Note 1: Pulse measurement.

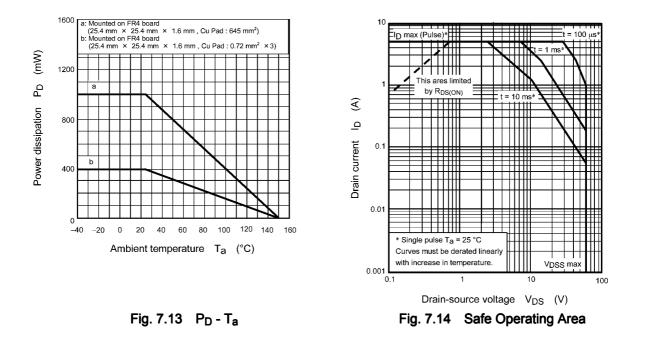
### 6. Marking



### 7. Characteristics Curves (Note)







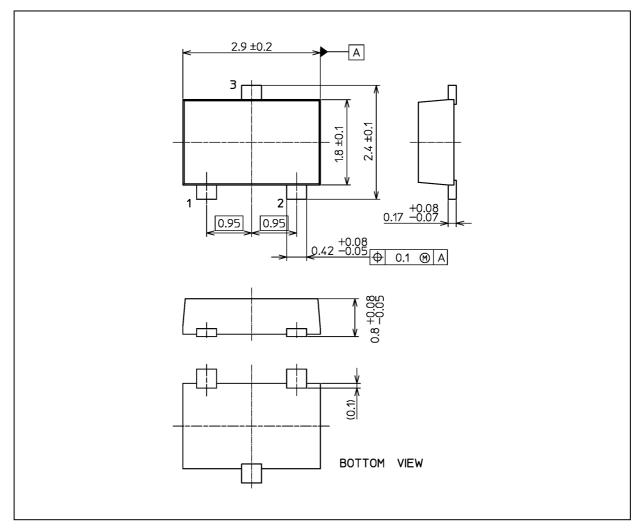
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### SSM3K318R

#### **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

	Package Name(s)
Nickname: SOT-23F	

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